

Welcome to [E-XFL.COM](#)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	49
Number of Gates	30000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agln030v2-zqng68

IGLOO nano Device Status

IGLOO nano Devices	Status	IGLOO nano-Z Devices	Status
AGLN010	Production		
AGLN015	Not recommended for new designs.		
AGLN020	Production		
		AGLN030Z	Not recommended for new designs.
AGLN060	Production	AGLN060Z	Not recommended for new designs.
AGLN125	Production	AGLN125Z	Not recommended for new designs.
AGLN250	Production	AGLN250Z	Not recommended for new designs.

Power per I/O Pin

**Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings
Applicable to IGLOO nano I/O Banks**

	VCCI (V)	Dynamic Power PAC9 (μ W/MHz) ¹
Single-Ended		
3.3 V LVTTL / 3.3 V LVCMOS	3.3	16.38
3.3 V LVTTL / 3.3 V LVCMOS – Schmitt Trigger	3.3	18.89
3.3 V LVCMOS Wide Range ²	3.3	16.38
3.3 V LVCMOS Wide Range – Schmitt Trigger	3.3	18.89
2.5 V LVCMOS	2.5	4.71
2.5 V LVCMOS – Schmitt Trigger	2.5	6.13
1.8 V LVCMOS	1.8	1.64
1.8 V LVCMOS – Schmitt Trigger	1.8	1.79
1.5 V LVCMOS (JESD8-11)	1.5	0.97
1.5 V LVCMOS (JESD8-11) – Schmitt Trigger	1.5	0.96
1.2 V LVCMOS ³	1.2	0.57
1.2 V LVCMOS – Schmitt Trigger ³	1.2	0.52
1.2 V LVCMOS Wide Range ³	1.2	0.57
1.2 V LVCMOS Wide Range – Schmitt Trigger ³	1.2	0.52

Notes:

1. PAC9 is the total dynamic power measured on V_{CCI} .
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.
3. Applicable to IGLOO nano V2 devices operating at $V_{CCI} \geq V_{CC}$.

**Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings¹
Applicable to IGLOO nano I/O Banks**

	C _{LOAD} (pF)	VCCI (V)	Dynamic Power PAC10 (μ W/MHz) ²
Single-Ended			
3.3 V LVTTL / 3.3 V LVCMOS	5	3.3	107.98
3.3 V LVCMOS Wide Range ³	5	3.3	107.98
2.5 V LVCMOS	5	2.5	61.24
1.8 V LVCMOS	5	1.8	31.28
1.5 V LVCMOS (JESD8-11)	5	1.5	21.50
1.2 V LVCMOS ⁴	5	1.2	15.22

Notes:

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. PAC10 is the total dynamic power measured on V_{CCI} .
3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.
4. Applicable for IGLOO nano V2 devices operating at $V_{CCI} \geq V_{CC}$.

Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices For IGLOO nano V2 Devices, 1.2 V Core Supply Voltage

Parameter	Definition	Device-Specific Dynamic Power (μ W/MHz)					
		AGLN250	AGLN125	AGLN060	AGLN020	AGLN015	AGLN010
PAC1	Clock contribution of a Global Rib	2.829	2.875	1.728	0	0	0
PAC2	Clock contribution of a Global Spine	1.731	1.265	1.268	2.562	2.562	1.685
PAC3	Clock contribution of a VersaTile row	0.957	0.963	0.967	0.862	0.862	0.858
PAC4	Clock contribution of a VersaTile used as a sequential module	0.098	0.098	0.098	0.094	0.094	0.091
PAC5	First contribution of a VersaTile used as a sequential module				0.045		
PAC6	Second contribution of a VersaTile used as a sequential module				0.186		
PAC7	Contribution of a VersaTile used as a combinatorial module				0.11		
PAC8	Average contribution of a routing net				0.45		
PAC9	Contribution of an I/O input pin (standard-dependent)				See Table 2-13 on page 2-9		
PAC10	Contribution of an I/O output pin (standard-dependent)				See Table 2-14 on page 2-9		
PAC11	Average contribution of a RAM block during a read operation			25.00		N/A	
PAC12	Average contribution of a RAM block during a write operation			30.00		N/A	
PAC13	Dynamic contribution for PLL			2.10		N/A	

Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO nano Devices For IGLOO nano V2 Devices, 1.2 V Core Supply Voltage

Parameter	Definition	Device-Specific Static Power (mW)					
		AGLN250	AGLN125	AGLN060	AGLN020	AGLN015	AGLN010
PDC1	Array static power in Active mode				See Table 2-12 on page 2-8		
PDC2	Array static power in Static (Idle) mode				See Table 2-12 on page 2-8		
PDC3	Array static power in Flash*Freeze mode				See Table 2-9 on page 2-7		
PDC4 ¹	Static PLL contribution			0.90		N/A	
PDC5	Bank quiescent power (VCCI-dependent) ²				See Table 2-12 on page 2-8		

Notes:

1. Minimum contribution of the PLL when running at lowest frequency.
2. For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or the SmartPower tool in Libero SoC.

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-19 on page 2-14.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-20 on page 2-14.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-20 on page 2-14. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = (PDC1 \text{ or } PDC2 \text{ or } PDC3) + N_{BANKS} * PDC5$$

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S-CELL} * PAC4) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the *IGLOO nano FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the *IGLOO nano FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-14.

F_{CLK} is the global clock signal frequency.

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = $(100\% + 50\% + 25\% + 12.5\% + \dots + 0.78125\%) / 8$

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-19 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-20 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

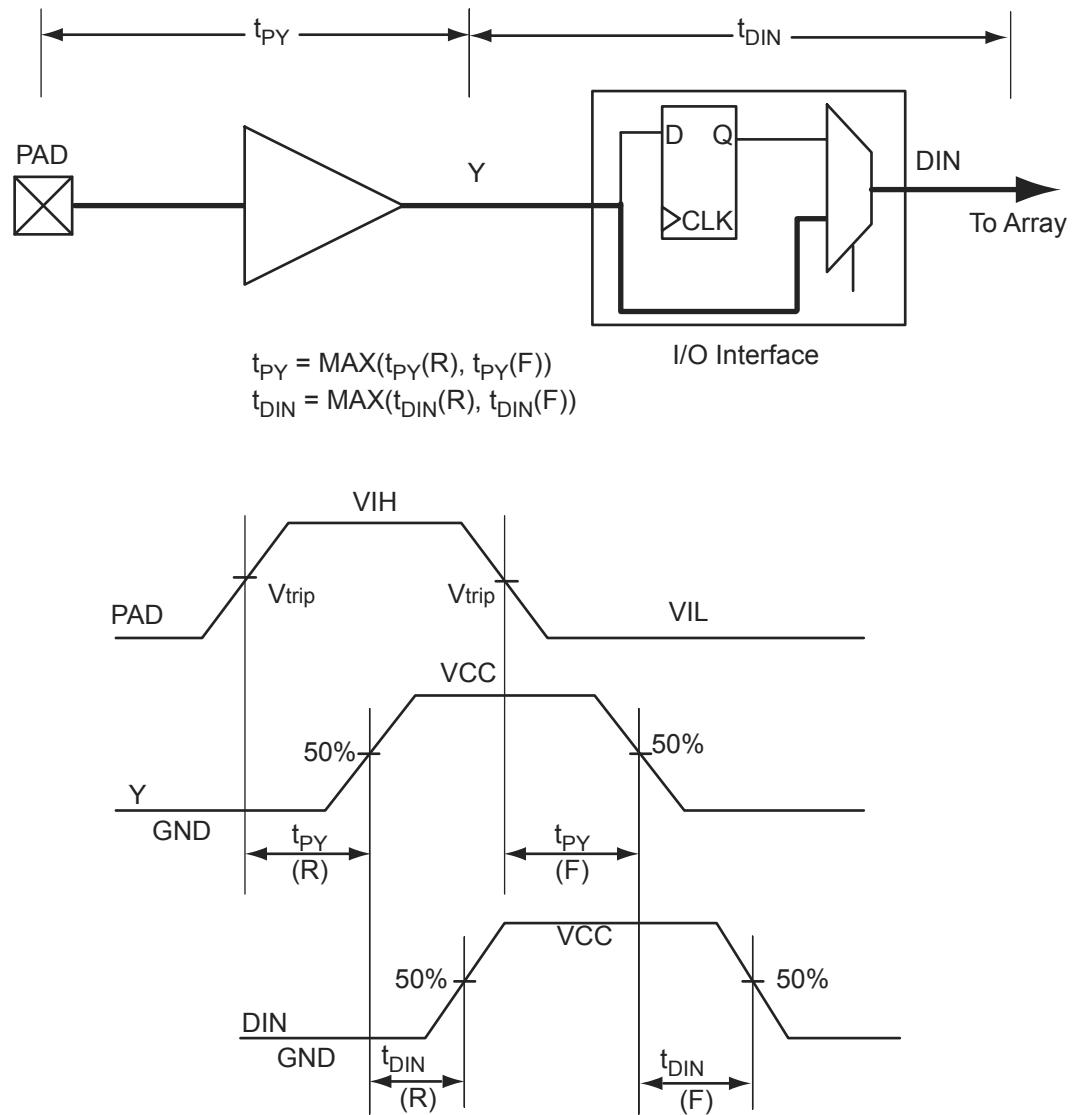


Figure 2-4 • Input Buffer Timing Model and Delays (example)

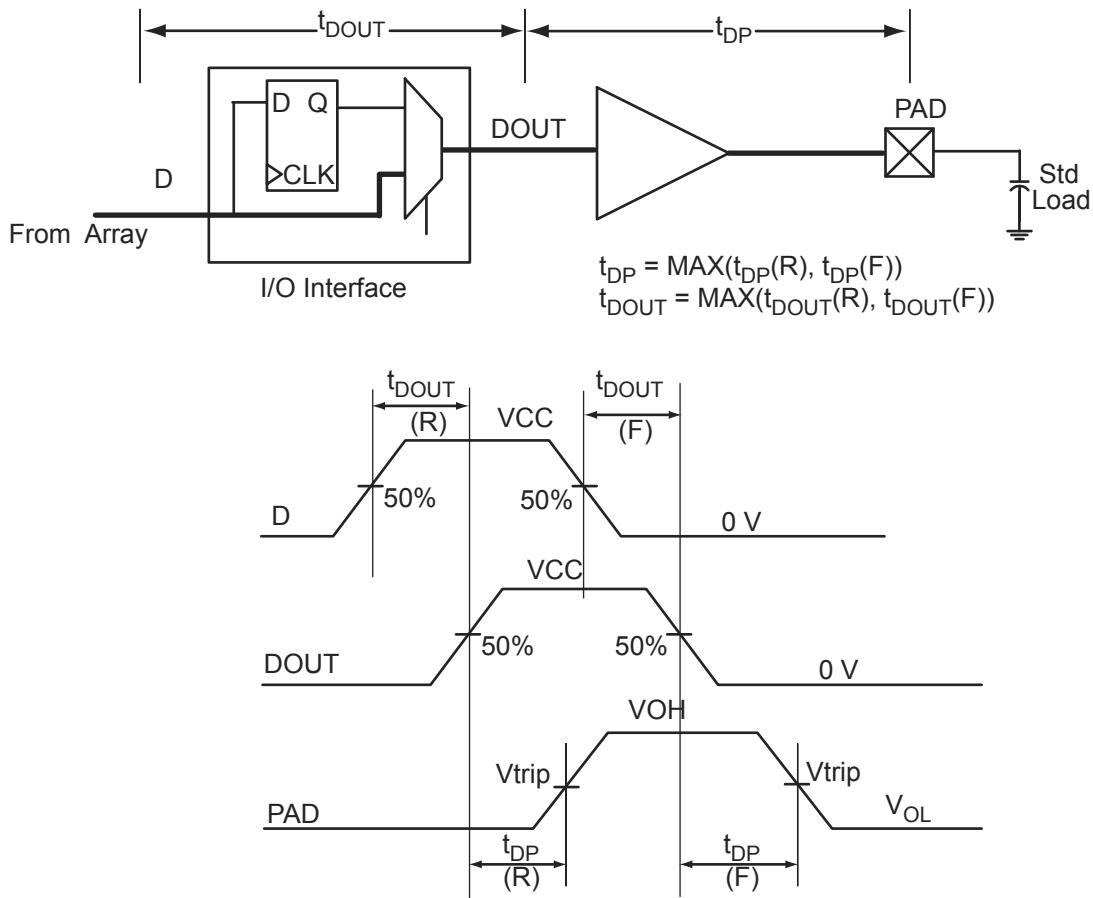


Figure 2-5 • Output Buffer Model and Delays (example)

3.3 V LVCMOS Wide Range

Table 2-40 • Minimum and Maximum DC Input and Output Levels for LVCMOS 3.3 V Wide Range

3.3 V LVCMOS Wide Range ¹	Equivalent Software Default Drive Strength Option ⁴	VIL		VIH		VOL	VOH	IOL	I _{OH}	IIL ²	I _{IH} ³
Drive Strength		Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	μA	μA	μA ⁵	μA ⁵
100 μA	2 mA	-0.3	0.8	2	3.6	0.2	VCCI - 0.2	100	100	10	10
100 μA	4 mA	-0.3	0.8	2	3.6	0.2	VCCI - 0.2	100	100	10	10
100 μA	6 mA	-0.3	0.8	2	3.6	0.2	VCCI - 0.2	100	100	10	10
100 μA	8 mA	-0.3	0.8	2	3.6	0.2	VCCI - 0.2	100	100	10	10

Notes:

1. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V Wide Range, as specified in the JEDEC JESD8-B specification.
2. I_{IL} is the input leakage current per I/O pin over recommended operating conditions where $-0.3 < VIN < VIL$.
3. I_{IH} is the input leakage current per I/O pin over recommended operating conditions where $VIH < VIN < VCCI$. Input current is larger when operating outside recommended ranges.
4. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100 \mu A$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
5. Currents are measured at 85°C junction temperature.
6. Software default selection is highlighted in gray.

1.2 V LVC MOS Wide Range

Table 2-67 • Minimum and Maximum DC Input and Output Levels

1.2 V LVC MOS Wide Range	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
1 mA	-0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI - 0.1	100	100	10	13	10	10

Notes:

1. I_{IL} is the input leakage current per I/O pin over recommended operating conditions where $-0.3 < VIN < VIL$.
2. I_{IH} is the input leakage current per I/O pin over recommended operating conditions where $VIH < VIN < VCCI$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Applicable to IGLOO nano V2 devices operating at $VCCI \geq VCC$.
6. Software default selection highlighted in gray.

Timing Characteristics

Applies to 1.2 V DC Core Voltage

Table 2-68 • 1.2 V LVC MOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $VCC = 1.14\text{ V}$, Worst-Case $VCCI = 1.14\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
100 μA	1 mA	STD	1.55	8.30	0.26	1.56	2.27	1.10	7.97	7.54	2.56	2.55	ns

Notes:

1. The minimum drive strength for any LVC MOS 1.2 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-69 • 1.2 V LVC MOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $VCC = 1.14\text{ V}$, Worst-Case $VCCI = 1.14\text{ V}$

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{PYS}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	Units
100 μA	1 mA	STD	1.55	3.50	0.26	1.56	2.27	1.10	3.37	3.10	2.55	2.66	ns

Notes:

1. The minimum drive strength for any LVC MOS 1.2 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.
3. Software default selection highlighted in gray.

Output Enable Register

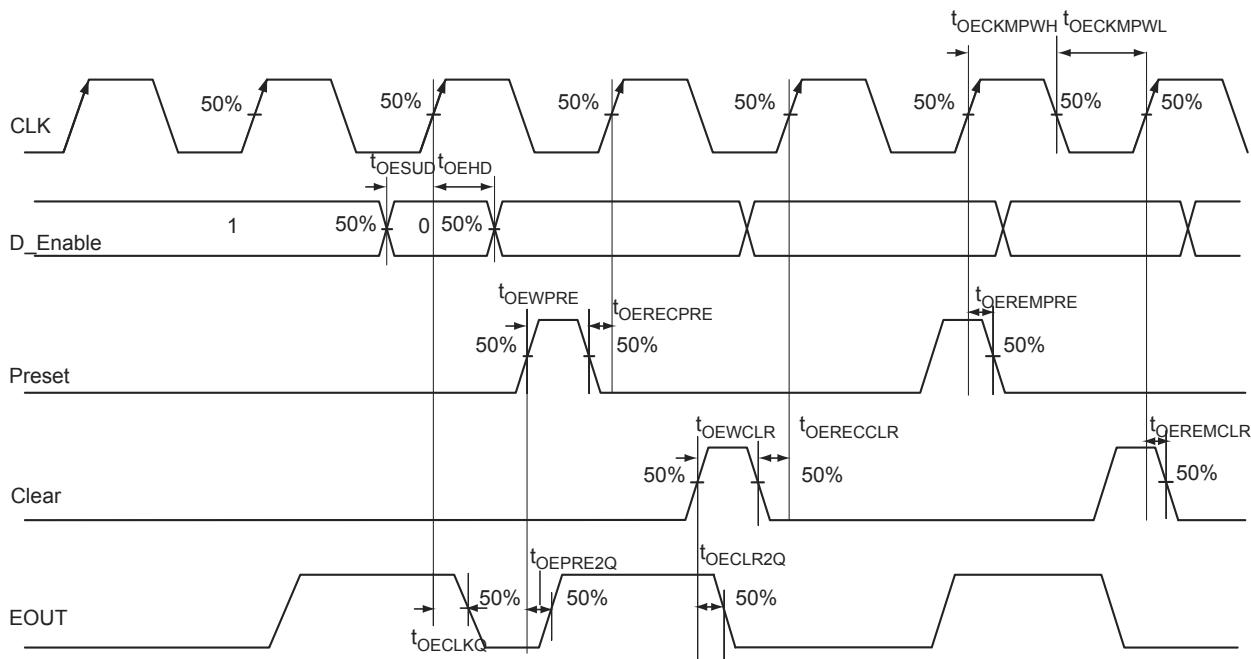


Figure 2-16 • Output Enable Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-76 • Output Enable Register Propagation Delays
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425 \text{ V}$

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.75	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.51	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.13	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.13	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width HIGH for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width LOW for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

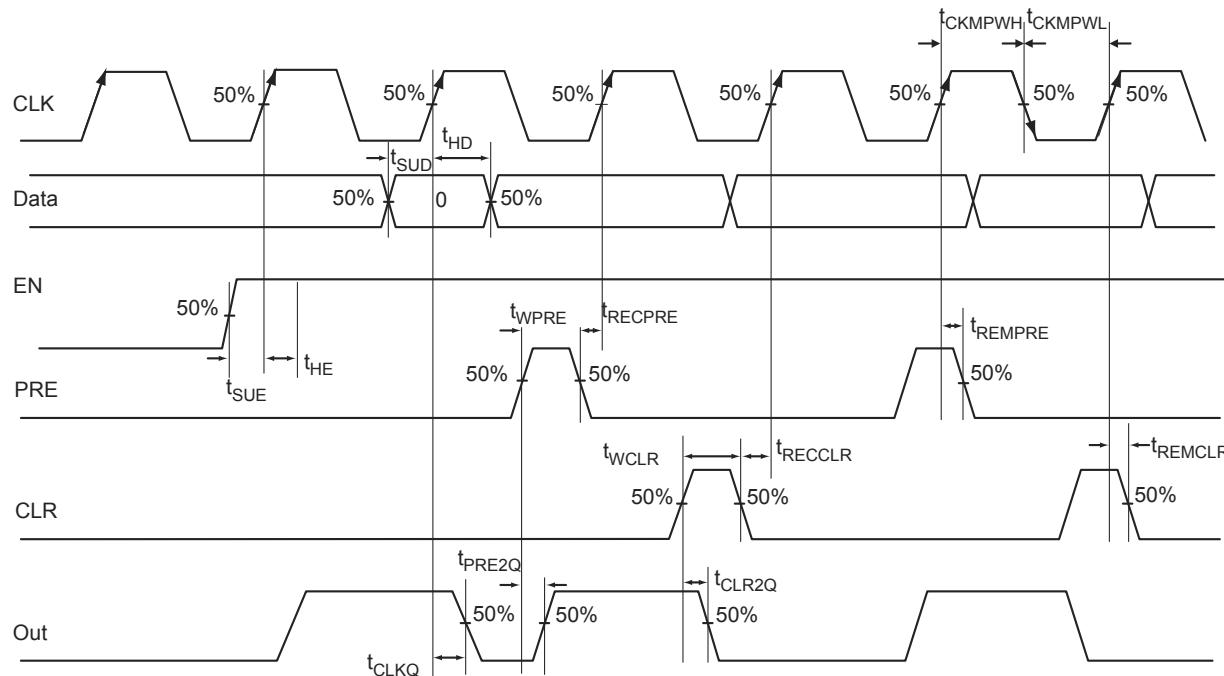


Figure 2-24 • Timing Model and Waveforms

Timing Characteristics

1.5 V DC Core Voltage

Table 2-86 • Register Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425 \text{ V}$

Parameter	Description	Std.	Units
t_{CLKQ}	Clock-to-Q of the Core Register	0.89	ns
t_{SUD}	Data Setup Time for the Core Register	0.81	ns
t_{HD}	Data Hold Time for the Core Register	0.00	ns
t_{SUE}	Enable Setup Time for the Core Register	0.73	ns
t_{HE}	Enable Hold Time for the Core Register	0.00	ns
t_{CLR2Q}	Asynchronous Clear-to-Q of the Core Register	0.60	ns
t_{PRE2Q}	Asynchronous Preset-to-Q of the Core Register	0.62	ns
t_{REMCRL}	Asynchronous Clear Removal Time for the Core Register	0.00	ns
t_{RECCRL}	Asynchronous Clear Recovery Time for the Core Register	0.24	ns
t_{REMPRE}	Asynchronous Preset Removal Time for the Core Register	0.00	ns
t_{RECPRE}	Asynchronous Preset Recovery Time for the Core Register	0.23	ns
t_{WCLR}	Asynchronous Clear Minimum Pulse Width for the Core Register	0.30	ns
t_{WPRE}	Asynchronous Preset Minimum Pulse Width for the Core Register	0.30	ns
t_{CKMPWH}	Clock Minimum Pulse Width HIGH for the Core Register	0.56	ns
t_{CKMPWL}	Clock Minimum Pulse Width LOW for the Core Register	0.56	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-92 • AGLN125 Global ResourceCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, $VCC = 1.425 \text{ V}$

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.36	1.71	ns
t_{RCKH}	Input High Delay for Global Clock	1.39	1.82	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-93 • AGLN250 Global ResourceCommercial-Case Conditions: $T_J = 70^\circ\text{C}$, $VCC = 1.425 \text{ V}$

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.39	1.73	ns
t_{RCKH}	Input High Delay for Global Clock	1.41	1.84	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Waveforms

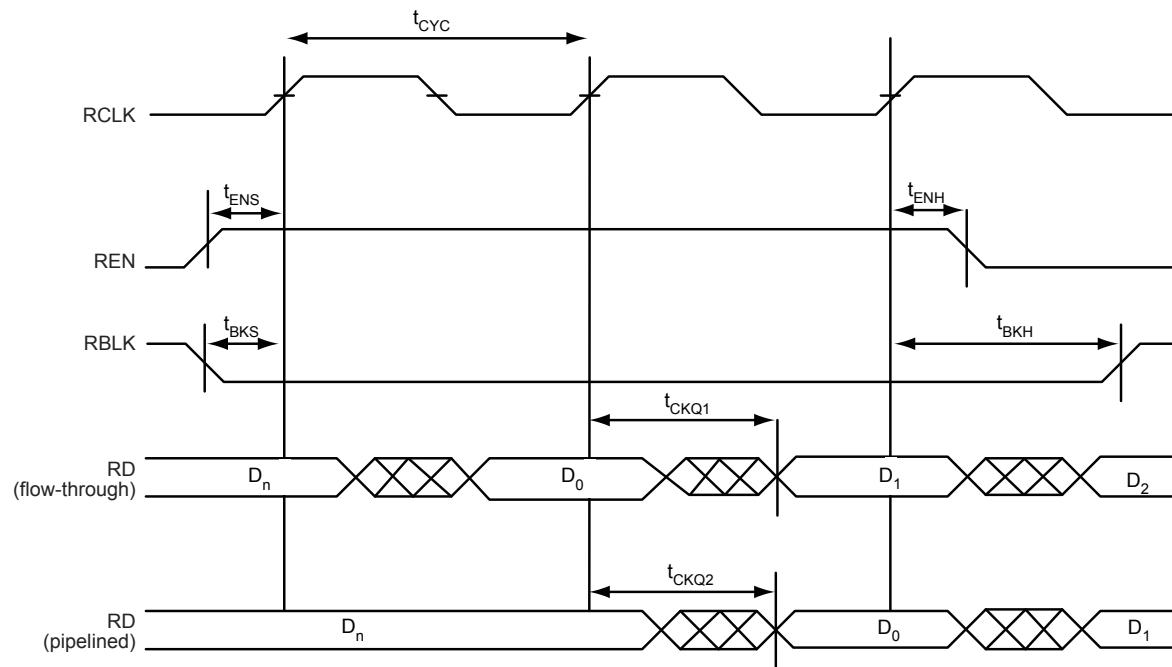


Figure 2-34 • FIFO Read

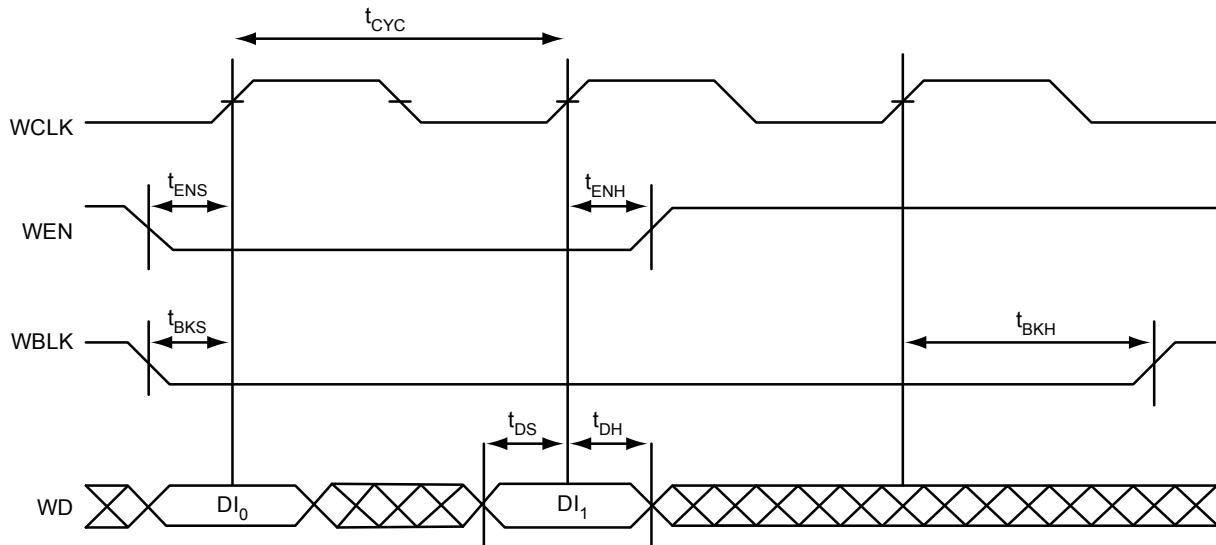


Figure 2-35 • FIFO Write

Embedded FlashROM Characteristics

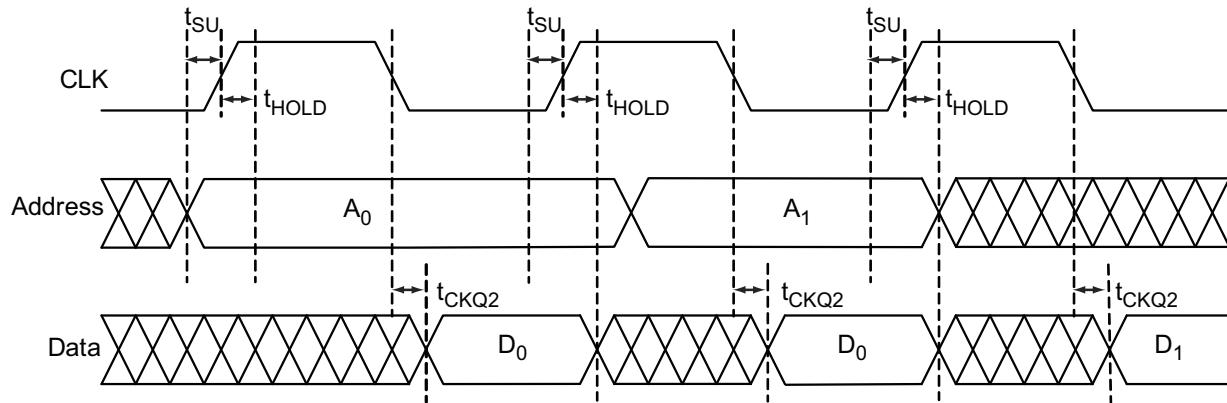


Figure 2-41 • Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-108 • Embedded FlashROM Access Time
 Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425 \text{ V}$

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.57	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	20.90	ns
F_{MAX}	Maximum Clock Frequency	15	MHz

1.2 V DC Core Voltage

Table 2-109 • Embedded FlashROM Access Time
 Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.14 \text{ V}$

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.59	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	35.74	ns
F_{MAX}	Maximum Clock Frequency	10	MHz

CS81	
Pin Number	AGLN060 Function
A1	GAA0/IO02RSB0
A2	GAA1/IO03RSB0
A3	GAC0/IO06RSB0
A4	IO09RSB0
A5	IO13RSB0
A6	IO18RSB0
A7	GBB0/IO21RSB0
A8	GBA1/IO24RSB0
A9	GBA2/IO25RSB0
B1	GAA2/IO95RSB1
B2	GAB0/IO04RSB0
B3	GAC1/IO07RSB0
B4	IO08RSB0
B5	IO15RSB0
B6	GBC0/IO19RSB0
B7	GBB1/IO22RSB0
B8	IO26RSB0
B9	GBB2/IO27RSB0
C1	GAB2/IO93RSB1
C2	IO94RSB1
C3	GND
C4	IO10RSB0
C5	IO17RSB0
C6	GND
C7	GBA0/IO23RSB0
C8	GBC2/IO29RSB0
C9	IO31RSB0
D1	GAC2/IO91RSB1
D2	IO92RSB1
D3	GFA2/IO80RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	GCC2/IO43RSB0

CS81	
Pin Number	AGLN060 Function
D8	GCC1/IO35RSB0
D9	GCC0/IO36RSB0
E1	GFB0/IO83RSB1
E2	GFB1/IO84RSB1
E3	GFA1/IO81RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GCA1/IO39RSB0
E8	GCA0/IO40RSB0
E9	GCB2/IO42RSB0
F1 ¹	VCCPLF
F2 ¹	VCOMPLF
F3	GND
F4	GND
F5	VCCIB1
F6	GND
F7	GDA1/IO49RSB0
F8	GDC1/IO45RSB0
F9	GDC0/IO46RSB0
G1	GEA0/IO69RSB1
G2	GEC1/IO74RSB1
G3	GEB1/IO72RSB1
G4	IO63RSB1
G5	IO60RSB1
G6	IO54RSB1
G7	GDB2/IO52RSB1
G8	VJTAG
G9	TRST
H1	GEA1/IO70RSB1
H2	FF/GEB2/IO67RSB1
H3	IO65RSB1
H4	IO62RSB1
H5	IO59RSB1

CS81	
Pin Number	AGLN060 Function
H6	IO56RSB1
H7 ²	GDA2/IO51RSB1
H8	TDI
H9	TDO
J1	GEA2/IO68RSB1
J2	GEC2/IO66RSB1
J3	IO64RSB1
J4	IO61RSB1
J5	IO58RSB1
J6	IO55RSB1
J7	TCK
J8	TMS
J9	VPUMP

Notes:

1. Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN060-CS81.
2. The bus hold attribute (hold previous I/O state in Flash*Freeze mode) is not supported for pin H7 in AGLN060-CS81.

CS81	
Pin Number	AGLN060Z Function
A1	GAA0/IO02RSB0
A2	GAA1/IO03RSB0
A3	GAC0/IO06RSB0
A4	IO09RSB0
A5	IO13RSB0
A6	IO18RSB0
A7	GBB0/IO21RSB0
A8	GBA1/IO24RSB0
A9	GBA2/IO25RSB0
B1	GAA2/IO95RSB1
B2	GAB0/IO04RSB0
B3	GAC1/IO07RSB0
B4	IO08RSB0
B5	IO15RSB0
B6	GBC0/IO19RSB0
B7	GBB1/IO22RSB0
B8	IO26RSB0
B9	GBB2/IO27RSB0
C1	GAB2/IO93RSB1
C2	IO94RSB1
C3	GND
C4	IO10RSB0
C5	IO17RSB0
C6	GND
C7	GBA0/IO23RSB0
C8	GBC2/IO29RSB0
C9	IO31RSB0
D1	GAC2/IO91RSB1
D2	IO92RSB1
D3	GFA2/IO80RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	GCC2/IO43RSB0

CS81	
Pin Number	AGLN060Z Function
D8	GCC1/IO35RSB0
D9	GCC0/IO36RSB0
E1	GFB0/IO83RSB1
E2	GFB1/IO84RSB1
E3	GFA1/IO81RSB1
E4	VCCIB1
E5	VCC
E6	VCCIB0
E7	GCA1/IO39RSB0
E8	GCA0/IO40RSB0
E9	GCB2/IO42RSB0
F1 ¹	VCCPLF
F2 ¹	VCOMPLF
F3	GND
F4	GND
F5	VCCIB1
F6	GND
F7	GDA1/IO49RSB0
F8	GDC1/IO45RSB0
F9	GDC0/IO46RSB0
G1	GEA0/IO69RSB1
G2	GEC1/IO74RSB1
G3	GEB1/IO72RSB1
G4	IO63RSB1
G5	IO60RSB1
G6	IO54RSB1
G7	GDB2/IO52RSB1
G8	VJTAG
G9	TRST
H1	GEA1/IO70RSB1
H2	FF/GEB2/IO67RSB1
H3	IO65RSB1
H4	IO62RSB1
H5	IO59RSB1

CS81	
Pin Number	AGLN060Z Function
H6	IO56RSB1
H7 ²	GDA2/IO51RSB1
H8	TDI
H9	TDO
J1	GEA2/IO68RSB1
J2	GEC2/IO66RSB1
J3	IO64RSB1
J4	IO61RSB1
J5	IO58RSB1
J6	IO55RSB1
J7	TCK
J8	TMS
J9	VPUMP

Notes:

1. Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN060Z-CS81.
2. The bus hold attribute (hold previous I/O state in Flash*Freeze mode) is not supported for pin H7 in AGLN060Z-CS81.

CS81	
Pin Number	AGLN250 Function
A1	GAA0/IO00RSB0
A2	GAA1/IO01RSB0
A3	GAC0/IO04RSB0
A4	IO07RSB0
A5	IO09RSB0
A6	IO12RSB0
A7	GBB0/IO16RSB0
A8	GBA1/IO19RSB0
A9	GBA2/IO20RSB1
B1	GAA2/IO67RSB3
B2	GAB0/IO02RSB0
B3	GAC1/IO05RSB0
B4	IO06RSB0
B5	IO10RSB0
B6	GBC0/IO14RSB0
B7	GBB1/IO17RSB0
B8	IO21RSB1
B9	GBB2/IO22RSB1
C1	GAB2/IO65RSB3
C2	IO66RSB3
C3	GND
C4	IO08RSB0
C5	IO11RSB0
C6	GND
C7	GBA0/IO18RSB0
C8	GBC2/IO23RSB1
C9	IO24RSB1
D1	GAC2/IO63RSB3
D2	IO64RSB3
D3	GFA2/IO56RSB3
D4	VCC
D5	VCCIB0
D6	GND
D7	IO30RSB1
D8	GCC1/IO25RSB1
D9	GCC0/IO26RSB1

CS81	
Pin Number	AGLN250 Function
E1	GFB0/IO59RSB3
E2	GFB1/IO60RSB3
E3	GFA1/IO58RSB3
E4	VCCIB3
E5	VCC
E6	VCCIB1
E7	GCA0/IO28RSB1
E8	GCA1/IO27RSB1
E9	GCB2/IO29RSB1
F1	VCCPLF
F2	VCOMPLF
F3	GND
F4	GND
F5	VCCIB2
F6	GND
F7	GDA1/IO33RSB1
F8	GDC1/IO31RSB1
F9	GDC0/IO32RSB1
G1	GEA0/IO51RSB3
G2	GEC1/IO54RSB3
G3	GEC0/IO53RSB3
G4	IO45RSB2
G5	IO42RSB2
G6	IO37RSB2
G7	GDB2/IO35RSB2
G8	VJTAG
G9	TRST
H1	GEA1/IO52RSB3
H2	FF/GEB2/IO49RSB2
H3	IO47RSB2
H4	IO44RSB2
H5	IO41RSB2
H6	IO39RSB2
H7	GDA2/IO34RSB2
H8	TDI
H9	TDO

CS81	
Pin Number	AGLN250 Function
J1	GEA2/IO50RSB2
J2	GEC2/IO48RSB2
J3	IO46RSB2
J4	IO43RSB2
J5	IO40RSB2
J6	IO38RSB2
J7	TCK
J8	TMS
J9	VPUMP

Note: * Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN250-CS81.

VQ100	
Pin Number	AGLN030Z Function
1	GND
2	IO82RSB1
3	IO81RSB1
4	IO80RSB1
5	IO79RSB1
6	IO78RSB1
7	IO77RSB1
8	IO76RSB1
9	GND
10	IO75RSB1
11	IO74RSB1
12	GEC0/IO73RSB1
13	GEA0/IO72RSB1
14	GEB0/IO71RSB1
15	IO70RSB1
16	IO69RSB1
17	VCC
18	VCCIB1
19	IO68RSB1
20	IO67RSB1
21	IO66RSB1
22	IO65RSB1
23	IO64RSB1
24	IO63RSB1
25	IO62RSB1
26	IO61RSB1
27	FF/IO60RSB1
28	IO59RSB1
29	IO58RSB1
30	IO57RSB1
31	IO56RSB1
32	IO55RSB1
33	IO54RSB1
34	IO53RSB1
35	IO52RSB1

VQ100	
Pin Number	AGLN030Z Function
36	IO51RSB1
37	VCC
38	GND
39	VCCIB1
40	IO49RSB1
41	IO47RSB1
42	IO46RSB1
43	IO45RSB1
44	IO44RSB1
45	IO43RSB1
46	IO42RSB1
47	TCK
48	TDI
49	TMS
50	NC
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	IO41RSB0
58	IO40RSB0
59	IO39RSB0
60	IO38RSB0
61	IO37RSB0
62	IO36RSB0
63	GDB0/IO34RSB0
64	GDA0/IO33RSB0
65	GDC0/IO32RSB0
66	VCCIB0
67	GND
68	VCC
69	IO31RSB0
70	IO30RSB0

VQ100	
Pin Number	AGLN030Z Function
71	IO29RSB0
72	IO28RSB0
73	IO27RSB0
74	IO26RSB0
75	IO25RSB0
76	IO24RSB0
77	IO23RSB0
78	IO22RSB0
79	IO21RSB0
80	IO20RSB0
81	IO19RSB0
82	IO18RSB0
83	IO17RSB0
84	IO16RSB0
85	IO15RSB0
86	IO14RSB0
87	VCCIB0
88	GND
89	VCC
90	IO12RSB0
91	IO10RSB0
92	IO08RSB0
93	IO07RSB0
94	IO06RSB0
95	IO05RSB0
96	IO04RSB0
97	IO03RSB0
98	IO02RSB0
99	IO01RSB0
100	IO00RSB0

VQ100	
Pin Number	AGLN250 Function
1	GND
2	GAA2/IO67RSB3
3	IO66RSB3
4	GAB2/IO65RSB3
5	IO64RSB3
6	GAC2/IO63RSB3
7	IO62RSB3
8	IO61RSB3
9	GND
10	GFB1/IO60RSB3
11	GFB0/IO59RSB3
12	VCOMPLF
13	GFA0/IO57RSB3
14	VCCPLF
15	GFA1/IO58RSB3
16	GFA2/IO56RSB3
17	VCC
18	VCCIB3
19	GFC2/IO55RSB3
20	GEC1/IO54RSB3
21	GEC0/IO53RSB3
22	GEA1/IO52RSB3
23	GEA0/IO51RSB3
24	VMV3
25	GNDQ
26	GEA2/IO50RSB2
27	FF/GEB2/IO49RSB2
28	GEC2/IO48RSB2
29	IO47RSB2
30	IO46RSB2
31	IO45RSB2
32	IO44RSB2
33	IO43RSB2
34	IO42RSB2
35	IO41RSB2
36	IO40RSB2

VQ100	
Pin Number	AGLN250 Function
37	VCC
38	GND
39	VCCIB2
40	IO39RSB2
41	IO38RSB2
42	IO37RSB2
43	GDC2/IO36RSB2
44	GDB2/IO35RSB2
45	GDA2/IO34RSB2
46	GNDQ
47	TCK
48	TDI
49	TMS
50	VMV2
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO33RSB1
58	GDC0/IO32RSB1
59	GDC1/IO31RSB1
60	IO30RSB1
61	GCB2/IO29RSB1
62	GCA1/IO27RSB1
63	GCA0/IO28RSB1
64	GCC0/IO26RSB1
65	GCC1/IO25RSB1
66	VCCIB1
67	GND
68	VCC
69	IO24RSB1
70	GBC2/IO23RSB1
71	GBB2/IO22RSB1
72	IO21RSB1

VQ100	
Pin Number	AGLN250 Function
73	GBA2/IO20RSB1
74	VMV1
75	GNDQ
76	GBA1/IO19RSB0
77	GBA0/IO18RSB0
78	GBB1/IO17RSB0
79	GBB0/IO16RSB0
80	GBC1/IO15RSB0
81	GBC0/IO14RSB0
82	IO13RSB0
83	IO12RSB0
84	IO11RSB0
85	IO10RSB0
86	IO09RSB0
87	VCCIB0
88	GND
89	VCC
90	IO08RSB0
91	IO07RSB0
92	IO06RSB0
93	GAC1/IO05RSB0
94	GAC0/IO04RSB0
95	GAB1/IO03RSB0
96	GAB0/IO02RSB0
97	GAA1/IO01RSB0
98	GAA0/IO00RSB0
99	GNDQ
100	VMV0

Revision	Changes	Page
Revision 12 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34663).	I, 1-2
	Notes indicating that AGLN015 is not recommended for new designs have been added (SAR 35759).	III, IV
	Notes indicating that nano-Z devices are not recommended for new designs have been added. The "Devices Not Recommended For New Designs" section is new (SAR 36759).	
Revision 12 (continued)	The Y security option and Licensed DPA Logo were added to the "IGLOO nano Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34722).	IV
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry enables rapid, single-voltage (3.3 V) programming of IGLOO nano devices via an IEEE 1532 JTAG interface" (SAR 34683).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 34694).	1-9
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P _{CLOCK} " section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the <i>IGLOO nano FPGA Fabric User's Guide</i> (SAR 34732).	2-12
	Figure 2-4 has been modified for DIN waveform; the Rise and Fall time label has been changed to tDIN (37106).	2-16
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34885).	2-26, 2-20
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section, "3.3 V LVCMOS Wide Range" section and "1.2 V LVCMOS Wide Range" section tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 34765).	2-20, 2-29, 2-40
	Added values for minimum pulse width and removed the FRMAX row from Table 2-88 through Table 2-99 in the "Global Tree Timing Characteristics" section. Use the software to determine the FRMAX for the device you are using (SAR 36953).	2-64 to 2-69
	Table 2-100 • IGLOO nano CCC/PLL Specification and Table 2-101 • IGLOO nano CCC/PLL Specification were updated. A note was added indicating that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 34817).	2-70 and 2-71
	The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-36 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35754). Reference was made to a new application note, <i>Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs</i> , which covers these cases in detail (SAR 34865).	2-74, 2-77, 2-85
	The "Pin Descriptions" chapter has been added (SAR 34770).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 34770).	4-1